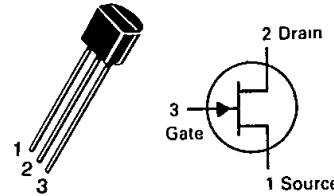


MPF256

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	± 30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Reverse Gate-Source Voltage	V_{GSR}	30	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.73	mW mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 10 \mu\text{Adc}, V_{DS} = 0$)	$V_{(BR)GSS}$	25	—	—	Vdc
Gate Reverse Current ($V_{GS} = 15 \text{ Vdc}, V_{DS} = 0$)	I_{GSS}	—	—	5.0	nAdc
Gate Source Cutoff Voltage ($V_{DS} = 15 \text{ Vdc}, I_D = 200 \mu\text{Adc}$)	$V_{GS(\text{off})}$	0.5	—	7.5	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0$)	I_{DSS^*}	3.0 6.0 11	—	7.0 13 18	mAdc

SMALL-SIGNAL CHARACTERISTICS

Forward Transfer Admittance ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ kHz}$)	$ V_{fsl} $	6.0	—	—	mmhos
Input Capacitance ($V_{DS} = 15 \text{ Vdc}, I_D = 10 \text{ mAdc}, f = 1.0 \text{ MHz}$)	C_{iss}	—	3.0	—	pF
Reverse Transfer Capacitance ($V_{DS} = 15 \text{ Vdc}, I_D = 10 \text{ mAdc}, f = 1.0 \text{ MHz}$)	C_{rss}	—	1.2	—	pF
Output Capacitance ($V_{DS} = 15 \text{ Vdc}, I_D = 10 \text{ mAdc}, f = 1.0 \text{ kHz}$)	C_{oss}	—	2.0	—	pF

FUNCTIONAL CHARACTERISTICS

Noise Figure ($V_{DS} = 15 \text{ Vdc}, R_S = 50 \text{ Ohms}$)	100 MHz 400 MHz	NF	— —	— —	2.0 4.0	dB
Common Source Power Gain ($V_{DS} = 15 \text{ Vdc}, R_S = 50 \text{ Ohms}$)	100 MHz 400 MHz	G_{ps}	20 12	— —	— —	dB

*To characterize these devices to narrower limits, the entire production lot is tested and divided into color-coded groups, with each color dot representing an I_{DSS} range.

When packaged for shipment, the colors are randomly selected and no specific color distribution is implied or guaranteed.

ELECTRICAL CHARACTERISTICS — Continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
Gate Threshold Voltage ($I_D = 250 \mu\text{A}$, $V_{DS} = V_{GS}$)	$V_{GS(\text{th})}$	2	—	4	Vdc
Static Drain-Source On-Resistance ⁽¹⁾ ($V_{GS} = 10 \text{ Vdc}$, $I_D = 0.4 \text{ A}$)	$r_{DS(\text{on})}$	—	—	0.8 1.2	Ohms
On-State Drain Current ⁽¹⁾ ($V_{GS} = 10 \text{ V}$, $V_{DS} = 5 \text{ V}$)	$I_{D(\text{on})}$	0.8 0.7	—	—	Adc
Forward Transconductance ⁽¹⁾ ($I_D = 0.4 \text{ A}$, $V_{DS} = 5 \text{ V}$)	g_{fs}	0.5	—	—	mhos
CAPACITANCE					
Input Capacitance	$(V_{DS} = 25 \text{ V}, V_{GS} = 0$ $f = 1 \text{ MHz}$)	C_{iss}	—	—	600
Output Capacitance		C_{oss}	—	—	300
Reverse Transfer Capacitance		C_{rss}	—	—	80
SWITCHING CHARACTERISTICS					
Turn-On Delay Time	$(V_{DS} = 0.5 V_{(BR)DSS}$, $I_D = 0.4 \text{ A}$, $Z_0 = 50 \Omega$)	$t_{d(\text{on})}$	—	—	40
Rise Time		t_r	—	—	60
Turn-Off Delay Time		$t_{d(\text{off})}$	—	—	100
Fall Time		t_f	—	—	60
SOURCE-DRAIN DIODE CHARACTERISTICS					
Diode Forward Voltage ($V_{GS} = 0$) $I_S = 0.8 \text{ A}$ IRFD220, IRFD221 $I_S = 0.7 \text{ A}$ IRFD222, IRFD223	V_{SD}	—	—	2 1.8	Vdc
Continuous Source Current, Body Diode	IRFD220, IRFD221 IRFD222, IRFD223	I_S	—	—	0.8 0.7
Pulsed Source Current, Body Diode		I_{SM}	—	—	6.4 5.6
Forward Turn-On Time	$(I_S = \text{Rated } I_S, V_{GS} = 0)$	t_{on}	negligible		
Reverse Recovery Time		t_{rr}	—	150	—

(1)Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

OUTLINE DIMENSIONS

